

De Haas-van Alphen oscillations in ZrSiS and HfSiS

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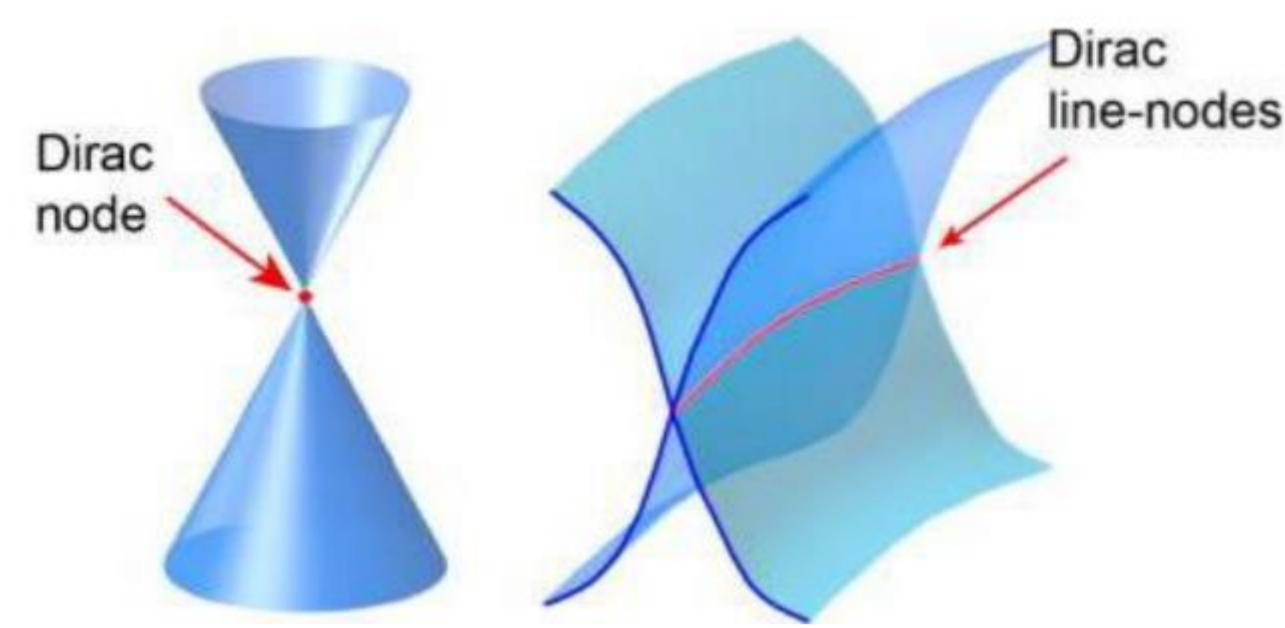
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Nodal line semimetal

Dirac nodal fermions physics:

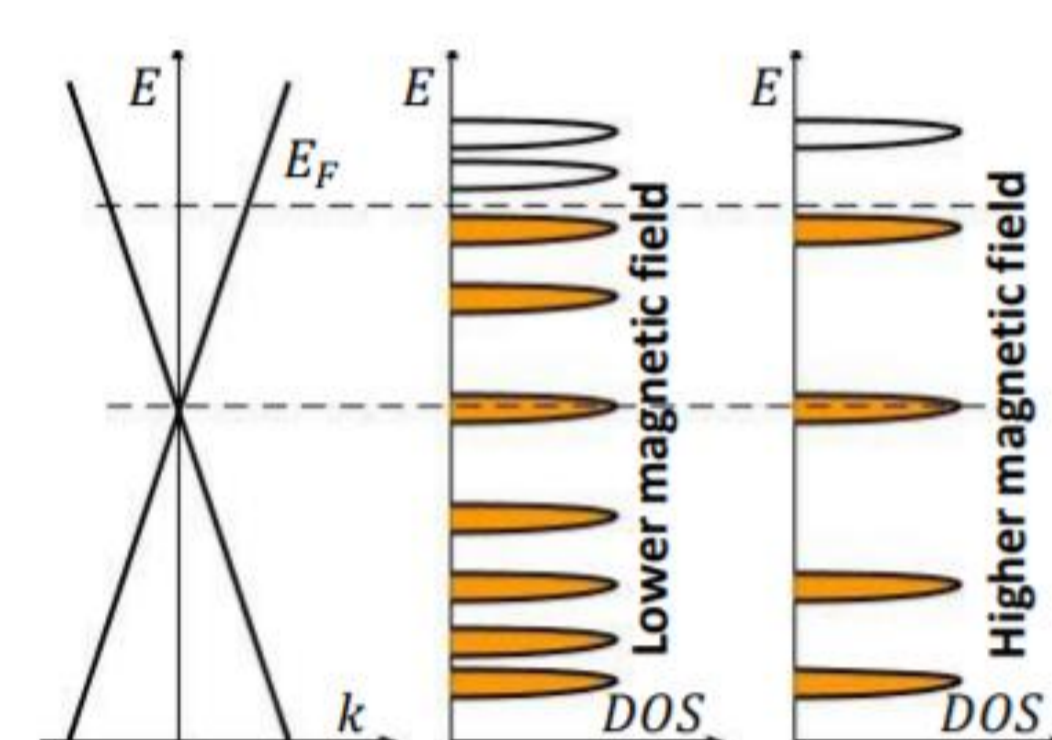
- Nontrivial topology
- Topologically protected surface states



Symmetry protected band degeneracies which form lines
Linear energy dispersion -> Dirac line nodes

Quantum oscillations

- Electrons in strong magnetic field
-> Landau levels
- Increasing field leads to periodical crossing of Landau levels and E_F
-> Oscillations of physical quantities with $1/B$
- Frequency of oscillations determined by the extremal cross sections of FS and plane normal to external field



Lifshitz-Kosevich equation

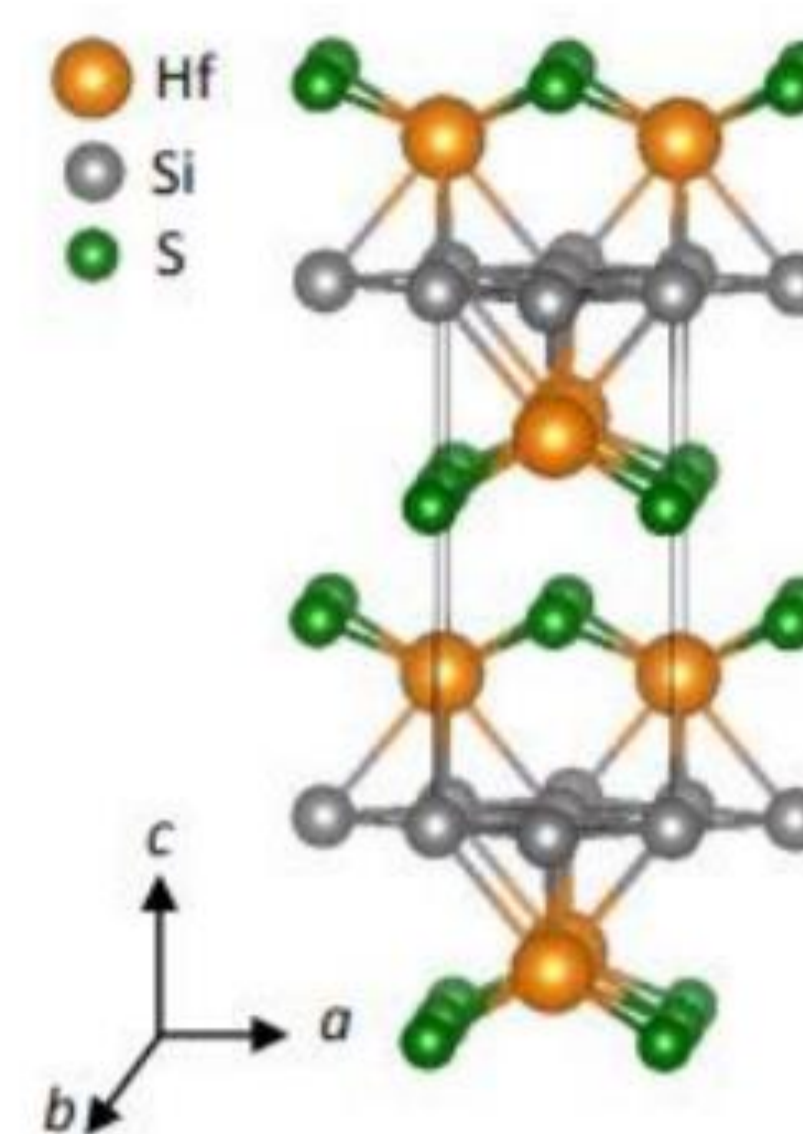
$$\Delta X(B, T) = A_0 A_T A_D A_S \left(\frac{B}{F}\right)^2 \cos\left[2\pi \frac{F}{B} + \phi\right]$$

$$A_T = -\frac{2\pi^2 \left(\frac{k_B T}{\hbar \omega_c}\right)}{\sinh\left(2\pi^2 \left(\frac{k_B T}{\hbar \omega_c}\right)\right)} \quad A_D = \exp\left(-2\pi^2 \left(\frac{k_B T_D}{\hbar \omega_c}\right)\right)$$

$$A_S = \cos\left[\pi g m_e / 2m_c\right]$$

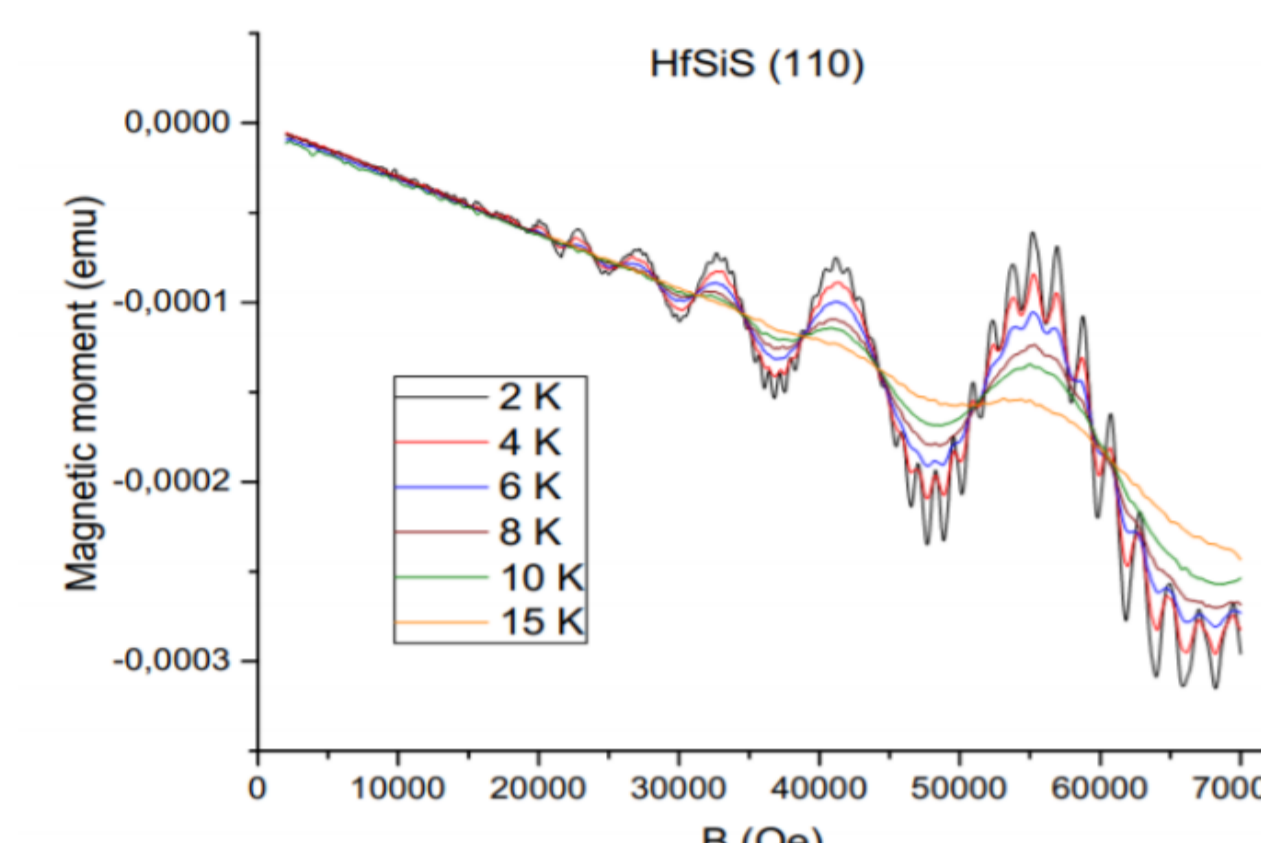
Quantum oscillations in magnetization -> de Haas-van Alphen oscillations

Hf_xZr_{1-x}SiS

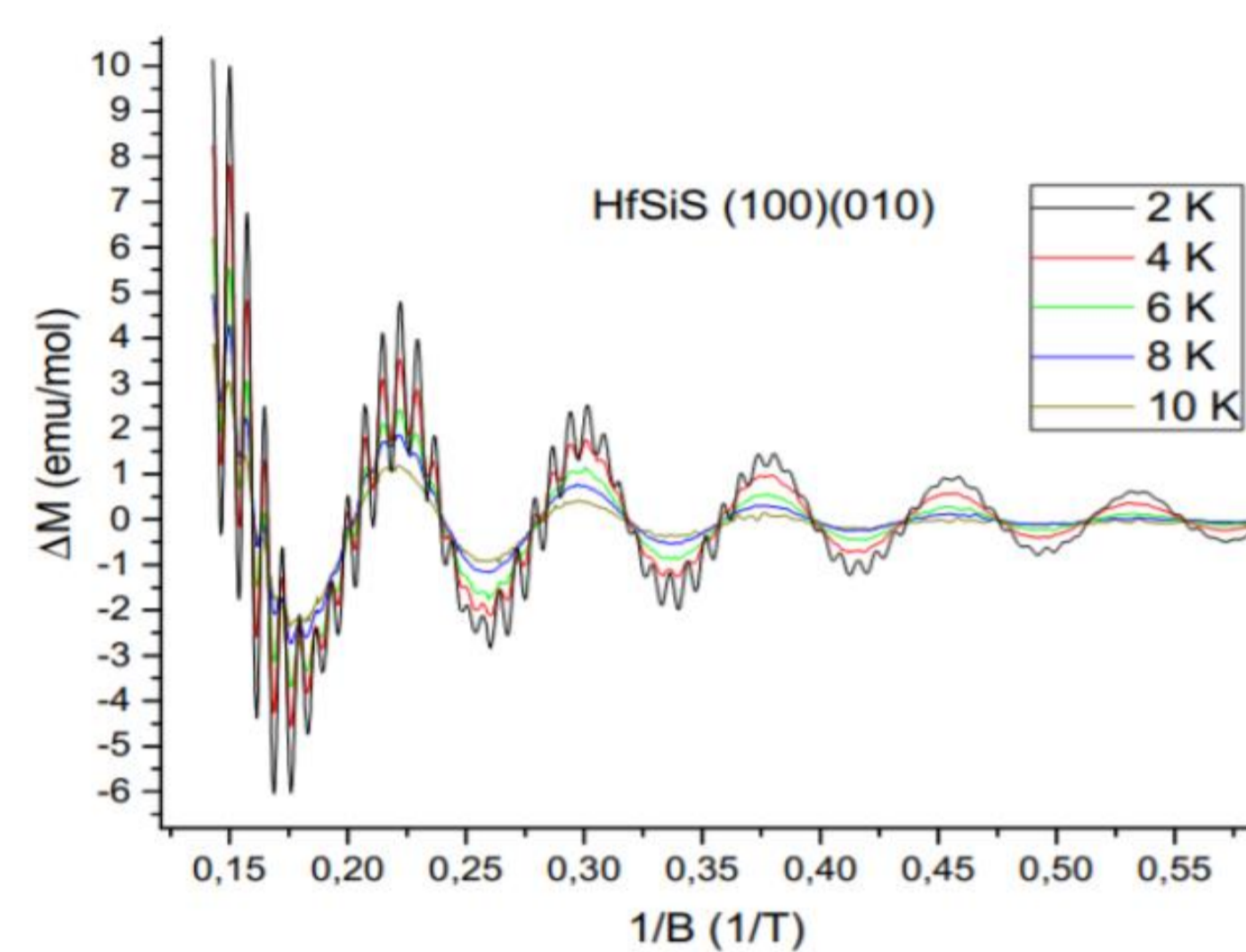


HfSiS and ZrSiS crystallize in same structure
-> possibility for substitution

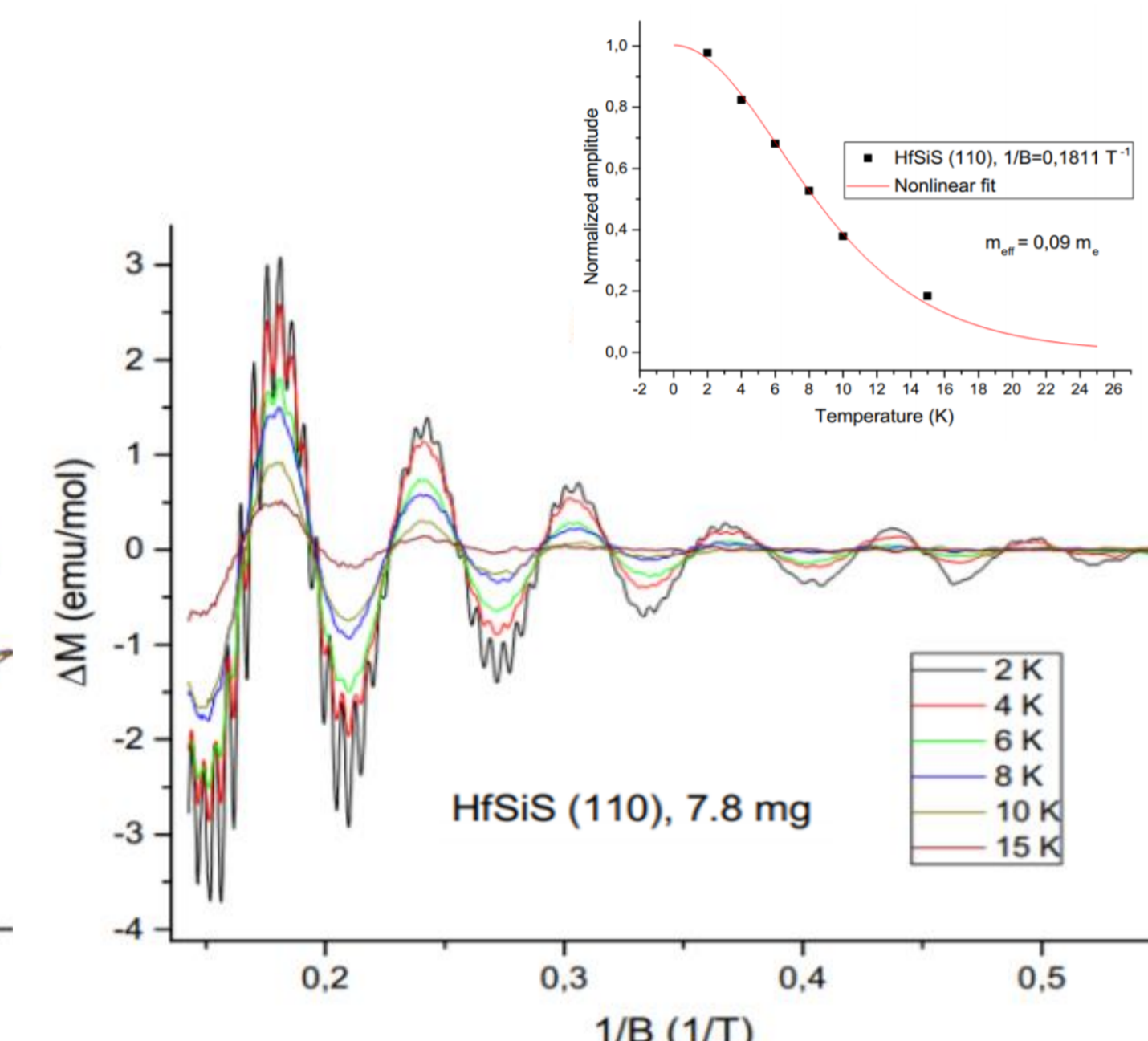
Magnetization data acquired with SQUID magnetometer up to 7 T for different ϕ and θ considering crystal symmetry



HfSiS

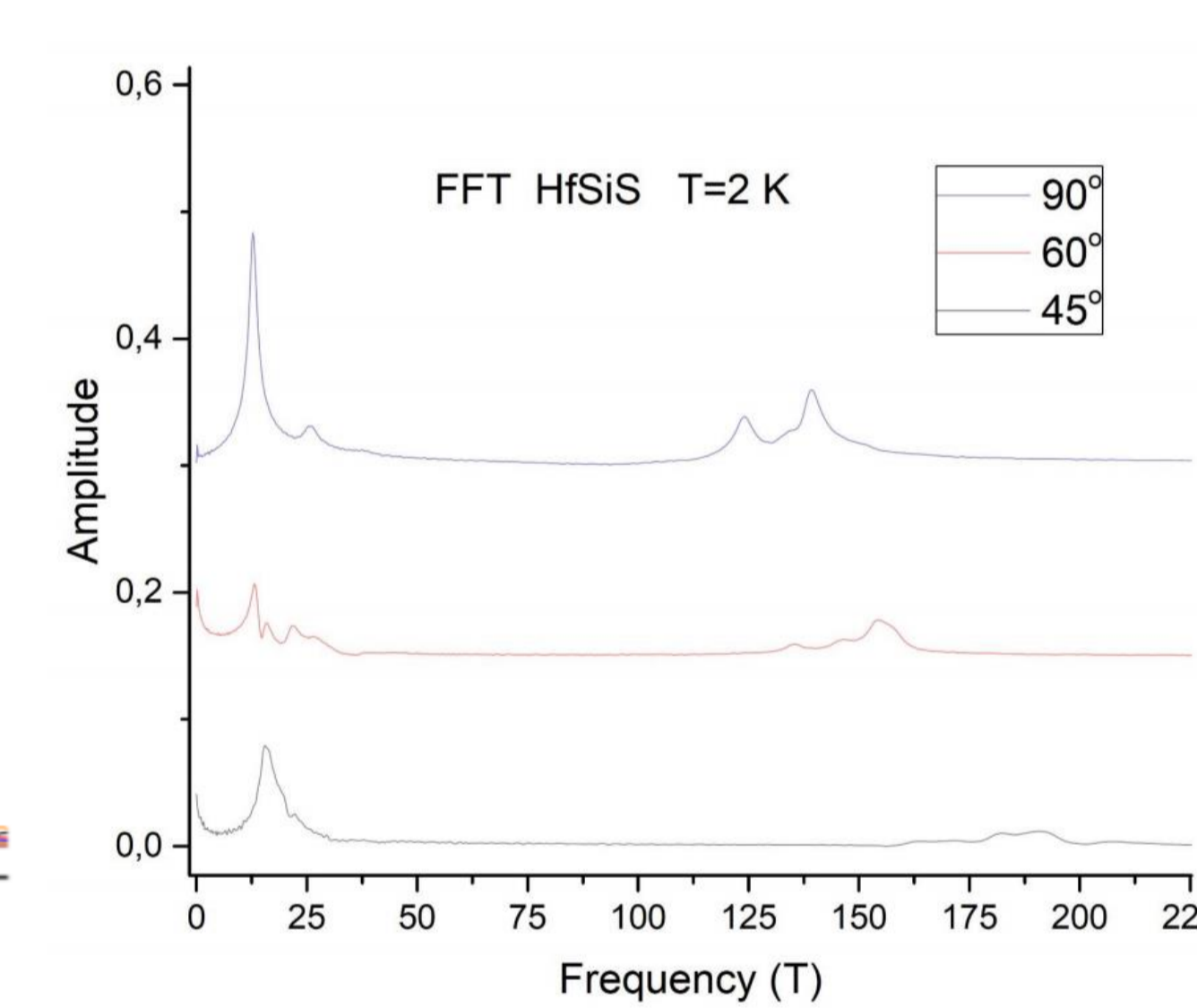
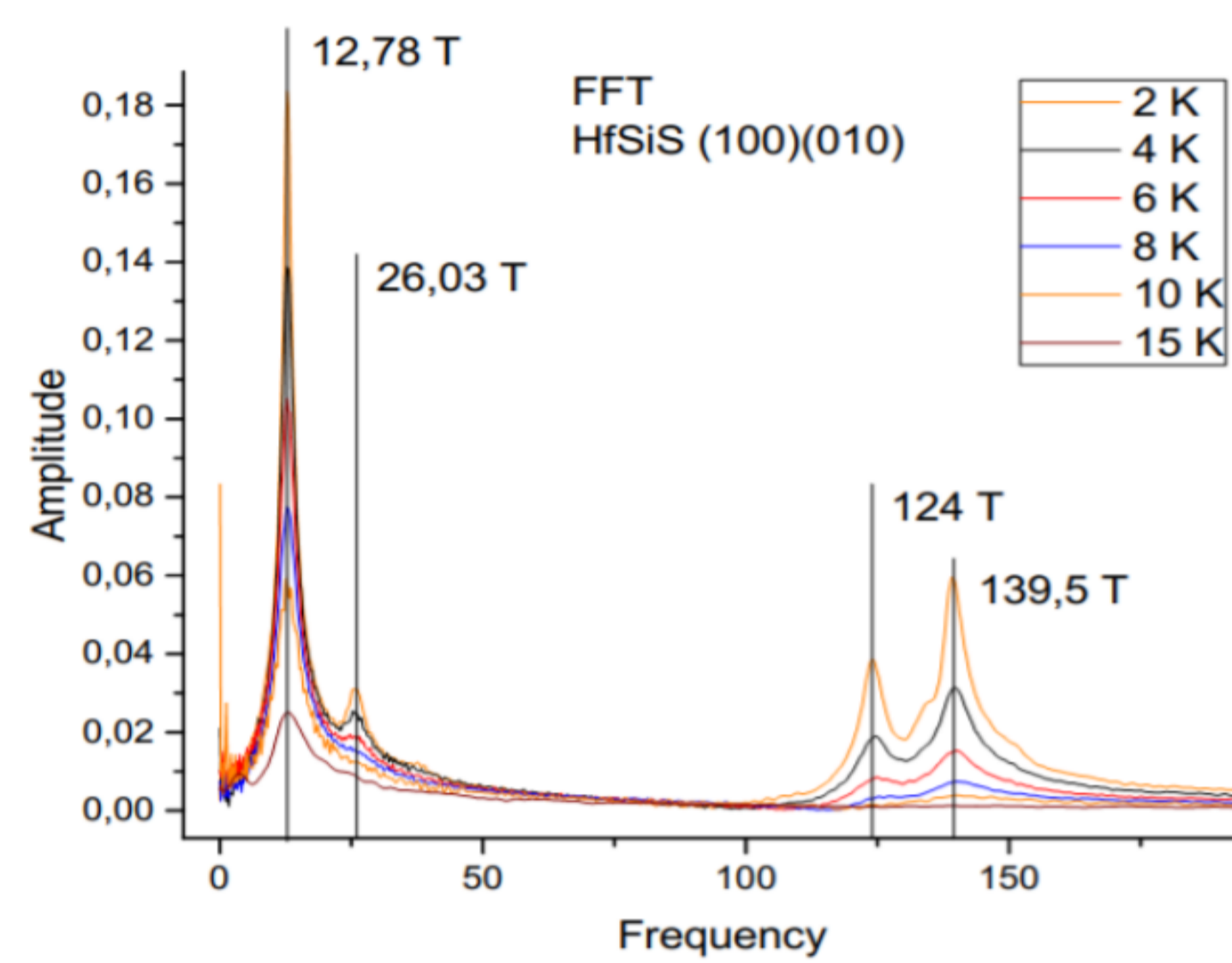


Interference of 'two groups' of frequencies

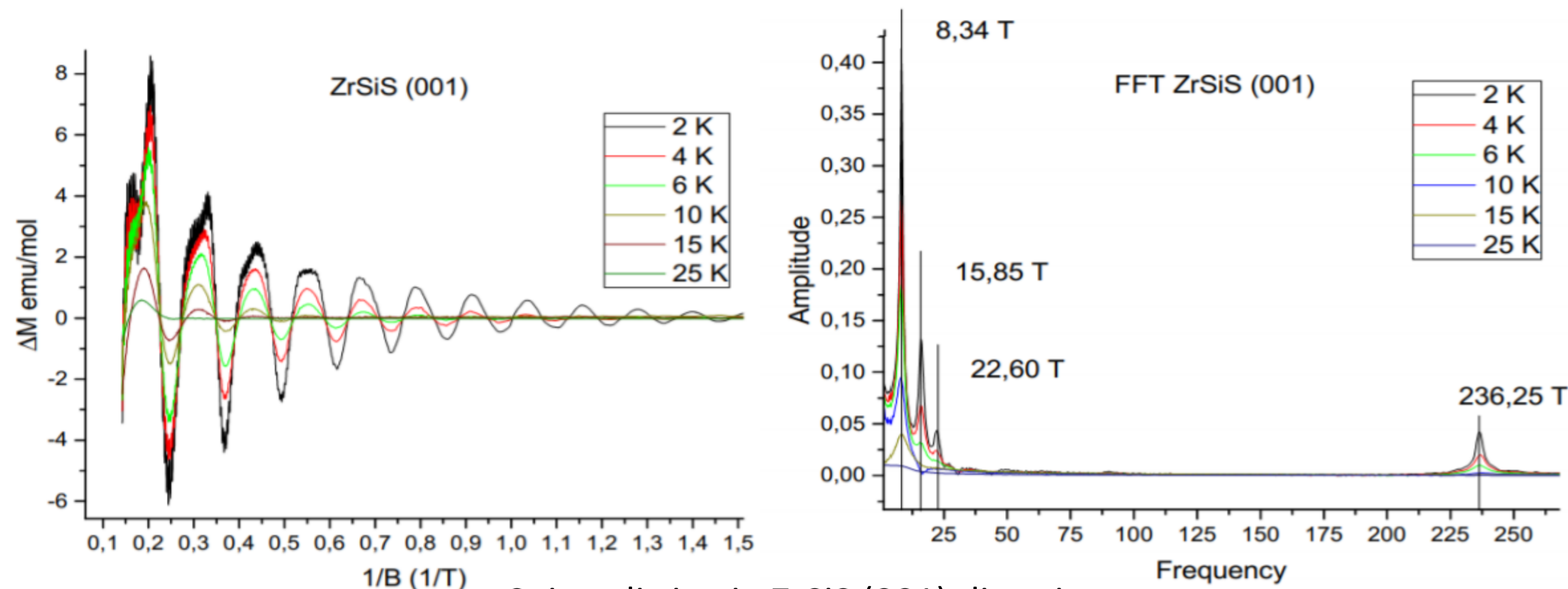


Effective mass can be obtained using LK equation

Propagation of frequencies for different ϕ

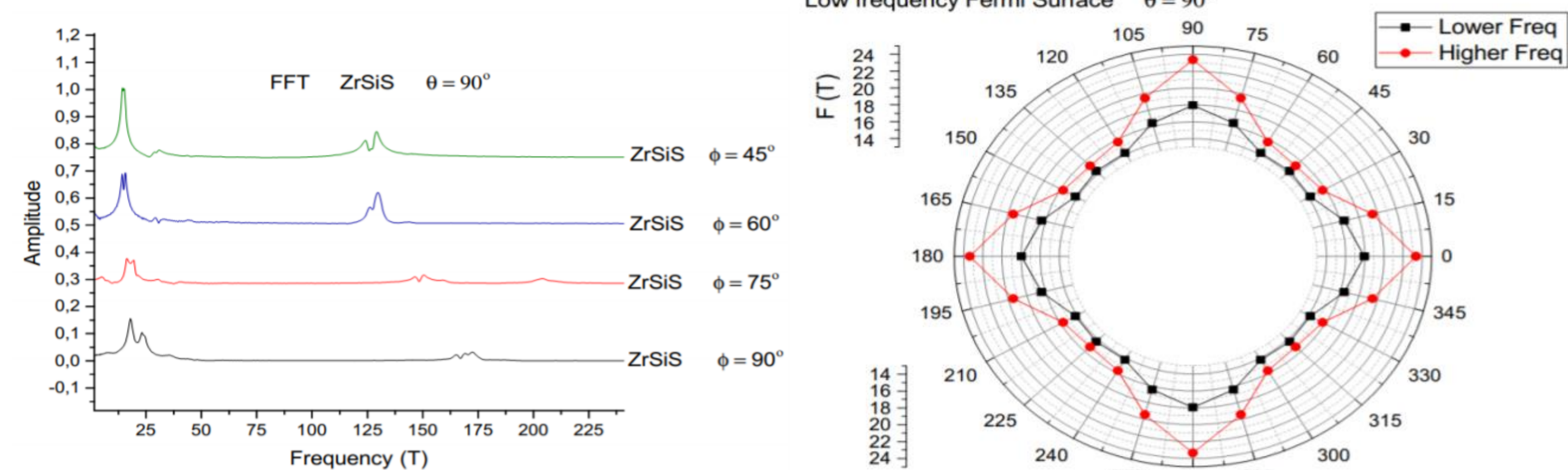


ZrSiS



Spin splitting in ZrSiS (001) direction

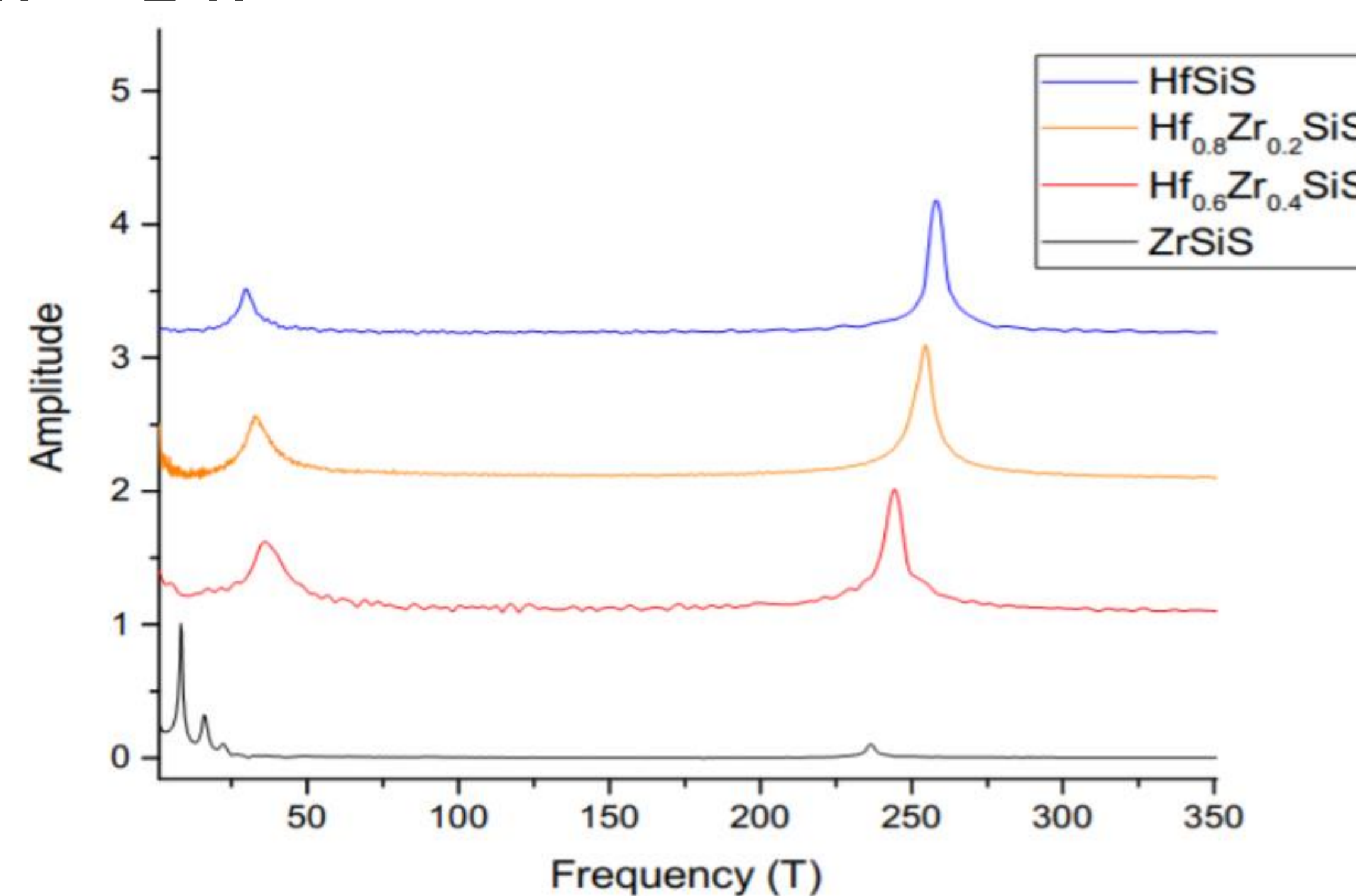
Reconstructing low frequency Fermi Surface by rotating the sample



Conclusion

- Magnetization in Hf_xZr_{1-x}SiS single crystal was measured with SQUID magnetometer up to 7 T for different angles ϕ and θ
- FFT of quantum oscillations shows two sets of frequencies: low frequencies (up to 40 T) and high frequencies between 100-250 T
- FS of selected crystal can be reconstructed from frequencies
- Measurement and synthesis of remaining Hf_xZr_{1-x}SiS compositions in progress

Hf_xZr_{1-x}SiS



Substitution effect on oscillations frequency in (001) direction
Measurement and synthesis of remaining compositions in progress

This work has been fully supported by Croatia Science Foundation under HRZZ projects 6216 and HRZZ IP-2018-1-8912